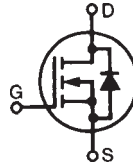


TrenchT2™ Power MOSFET

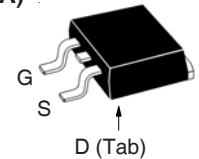
IXTA110N055T2 IXTP110N055T2

$V_{DSS} = 55V$
 $I_{D25} = 110A$
 $R_{DS(on)} \leq 6.6m\Omega$

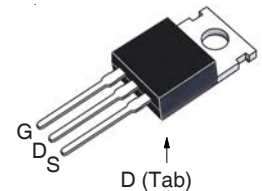
N-Channel Enhancement Mode
 Avalanche Rated



TO-263 (IXTA)



TO-220 (IXTP)



G = Gate D = Drain
 S = Source Tab = Drain

| Symbol | Test Conditions | Maximum Ratings | |
|---------------|---|--------------------|------------|
| V_{DSS} | $T_J = 25^\circ C$ to $175^\circ C$ | 55 | V |
| V_{DGR} | $T_J = 25^\circ C$ to $175^\circ C$, $R_{GS} = 1M\Omega$ | 55 | V |
| V_{GSM} | Transient | ± 20 | V |
| I_{D25} | $T_C = 25^\circ C$ | 110 | A |
| I_{DM} | $T_C = 25^\circ C$, Pulse Width Limited by T_{JM} | 300 | A |
| I_A | $T_C = 25^\circ C$ | 50 | A |
| E_{AS} | $T_C = 25^\circ C$ | 400 | mJ |
| P_D | $T_C = 25^\circ C$ | 180 | W |
| T_J | | -55 ... +175 | $^\circ C$ |
| T_{JM} | | 175 | $^\circ C$ |
| T_{stg} | | -55 ... +175 | $^\circ C$ |
| T_L | Maximum Lead Temperature for Soldering | 300 | $^\circ C$ |
| T_{SOLD} | 1.6 mm (0.062in.) from Case for 10s | 260 | $^\circ C$ |
| F_C | Mounting Force (TO-263) | 10..65 / 2.2..14.6 | N/lb |
| M_d | Mounting Torque (TO-220) | 1.13 / 10 | Nm/lb.in |
| Weight | TO-263 | 2.5 | g |
| | TO-220 | 3.0 | g |

Features

- International Standard Packages
- Avalanche Rated
- Low Package Inductance
- Fast Intrinsic Rectifier
- 175°C Operating Temperature
- High Current Handling Capability
- ROHS Compliant
- High Performance Trench Technology for extremely low $R_{DS(on)}$

Advantages

- High Power Density
- Easy to Mount
- Space Savings

Applications

- Automotive Engine Control
- Synchronous Buck Converter (for Notebook System Power & General Purpose Point & Load)
- DC/DC Converters
- High Current Switching Applications
- Power Train Management
- Distributed Power Architecture

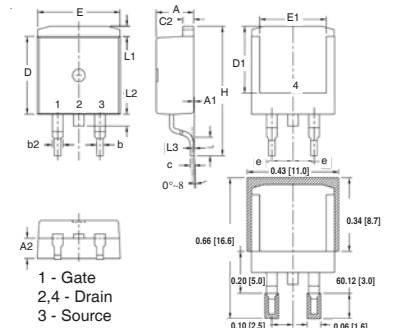
| Symbol | Test Conditions ($T_J = 25^\circ C$ Unless Otherwise Specified) | Characteristic Values | | |
|--------------|---|-----------------------|------|--------------------------|
| | | Min. | Typ. | Max. |
| BV_{DSS} | $V_{GS} = 0V$, $I_D = 250\mu A$ | 55 | | V |
| $V_{GS(th)}$ | $V_{DS} = V_{GS}$, $I_D = 250\mu A$ | 2.0 | | V |
| I_{GSS} | $V_{GS} = \pm 20V$, $V_{DS} = 0V$ | | | ± 200 nA |
| I_{DSS} | $V_{DS} = V_{DSS}$, $V_{GS} = 0V$ $T_J = 150^\circ C$ | | | 2 μA 200 μA |
| $R_{DS(on)}$ | $V_{GS} = 10V$, $I_D = 25A$, Notes 1 & 2 | 5.5 | 6.6 | m Ω |

| Symbol | Test Conditions | Characteristic Values | | |
|--------------|---|-----------------------|------|-----------|
| | | Min. | Typ. | Max. |
| g_{fs} | $V_{DS} = 10V, I_D = 55A$, Note 1 | 30 | 49 | S |
| C_{iss} | $V_{GS} = 0V, V_{DS} = 25V, f = 1MHz$ | | 3060 | pF |
| C_{oss} | | | 497 | pF |
| C_{rss} | | | 105 | pF |
| $t_{d(on)}$ | Resistive Switching Times $V_{GS} = 10V, V_{DS} = 30V, I_D = 25A$ $R_G = 5\Omega$ (External) | | 18 | ns |
| t_r | | | 25 | ns |
| $t_{d(off)}$ | | | 40 | ns |
| t_f | | | 23 | ns |
| $Q_{g(on)}$ | $V_{GS} = 10V, V_{DS} = 0.5 \cdot V_{DSS}, I_D = 25A$ | | 57 | nC |
| Q_{gs} | | | 16 | nC |
| Q_{gd} | | | 11 | nC |
| R_{thJC} | TO-220 | | | 0.82 °C/W |
| R_{thCS} | | 0.50 | | °C/W |

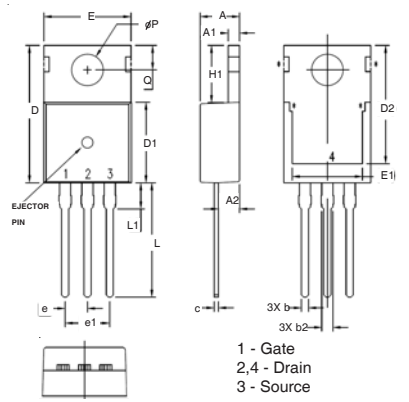
Source-Drain Diode

| Symbol | Test Conditions | Characteristic Values | | |
|----------|---|-----------------------|------|-------|
| | | Min. | Typ. | Max. |
| I_s | $V_{GS} = 0V$ | | | 110 A |
| I_{SM} | Repetitive, Pulse Width Limited by T_{JM} | | | 300 A |
| V_{SD} | $I_F = 25A, V_{GS} = 0V$, Note 1 | 0.84 | 1.00 | V |
| t_{rr} | $I_F = 50A, V_{GS} = 0V,$ $-di/dt = 100A/\mu s, V_R = 27V$ | | 38 | ns |
| I_{RM} | | | 2.4 | A |
| Q_{RM} | | | 46 | nC |

- Notes: 1. Pulse test, $t \leq 300\mu s$; duty cycle, $d \leq 2\%$.
 2. On through-hole packages, $R_{DS(on)}$ Kelvin test contact location must be 5mm or less from the package body.

TO-263 Outline


| SYM | INCHES | | MILLIMETER | |
|------|----------|------|------------|-------|
| | MIN | MAX | MIN | MAX |
| A | .170 | .185 | 4.30 | 4.70 |
| A1 | .000 | .008 | 0.00 | 0.20 |
| A2 | .091 | .098 | 2.30 | 2.50 |
| b | .028 | .035 | 0.70 | 0.90 |
| b2 | .046 | .060 | 1.18 | 1.52 |
| C | .018 | .024 | 0.45 | 0.60 |
| C2 | .049 | .060 | 1.25 | 1.52 |
| D | .340 | .370 | 8.63 | 9.40 |
| D1 | .300 | .327 | 7.62 | 8.30 |
| E | .380 | .410 | 9.65 | 10.41 |
| E1 | .270 | .330 | 6.86 | 8.38 |
| (E) | .100 BSC | | 2.54 BSC | |
| H | .580 | .620 | 14.73 | 15.75 |
| L | .075 | .105 | 1.91 | 2.67 |
| L1 | .039 | .060 | 1.00 | 1.52 |
| L2 | — | .070 | — | 1.77 |
| (L3) | .010 BSC | | 0.254 BSC | |

TO-220 Outline


| SYM | INCHES | | MILLIMETERS | |
|------|----------|------|-------------|-------|
| | MIN | MAX | MIN | MAX |
| A | .169 | .185 | 4.30 | 4.70 |
| A1 | .047 | .055 | 1.20 | 1.40 |
| A2 | .079 | .106 | 2.00 | 2.70 |
| b | .024 | .039 | 0.60 | 1.00 |
| b2 | .045 | .057 | 1.15 | 1.45 |
| c | .014 | .026 | 0.35 | 0.65 |
| D | .587 | .626 | 14.90 | 15.90 |
| D1 | .335 | .370 | 8.50 | 9.40 |
| (D2) | .500 | .531 | 12.70 | 13.50 |
| E | .382 | .406 | 9.70 | 10.30 |
| (E1) | .283 | .323 | 7.20 | 8.20 |
| e | .100 BSC | | 2.54 BSC | |
| e1 | .200 BSC | | 5.08 BSC | |
| H1 | .244 | .268 | 6.20 | 6.80 |
| L | .492 | .547 | 12.50 | 13.90 |
| L1 | .110 | .154 | 2.80 | 3.90 |
| ØP | .134 | .150 | 3.40 | 3.80 |
| Q | .106 | .126 | 2.70 | 3.20 |

IXYS Reserves the Right to Change Limits, Test Conditions, and Dimensions.

| | | | | | | | | | | |
|--|-----------|-----------|-----------|-----------|-------------|-------------|-------------|-------------|-------------|-------------|
| IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents: | 4,835,592 | 4,931,844 | 5,049,961 | 5,237,481 | 6,162,665 | 6,404,065B1 | 6,683,344 | 6,727,585 | 7,005,734B2 | 7,157,338B2 |
| | 4,860,072 | 5,017,508 | 5,063,307 | 5,381,025 | 6,259,123B1 | 6,534,343 | 6,710,405B2 | 6,759,692 | 7,063,975B2 | |
| | 4,881,106 | 5,034,796 | 5,187,117 | 5,486,715 | 6,306,728B1 | 6,583,505 | 6,710,463 | 6,771,478B2 | 7,071,537 | |

Fig. 1. Output Characteristics @ $T_J = 25^\circ\text{C}$

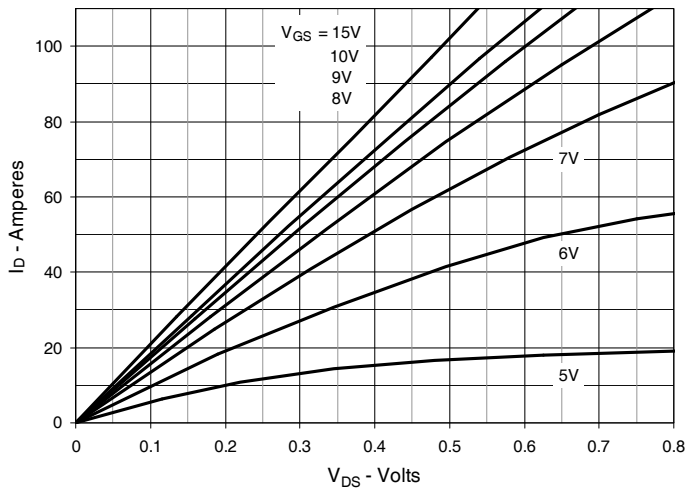


Fig. 2. Extended Output Characteristics @ $T_J = 25^\circ\text{C}$

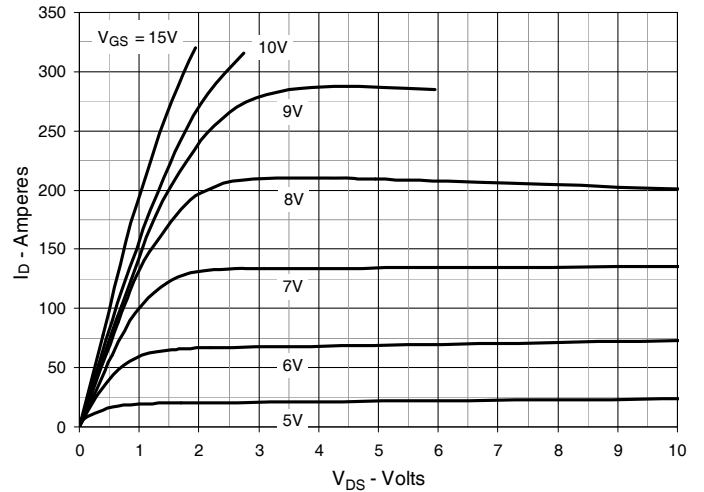


Fig. 3. Output Characteristics @ $T_J = 150^\circ\text{C}$

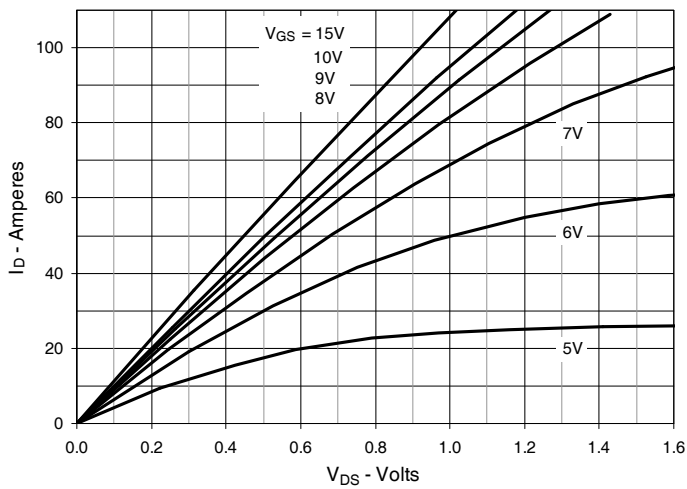


Fig. 4. $R_{DS(on)}$ Normalized to $I_D = 55\text{A}$ Value vs. Junction Temperature

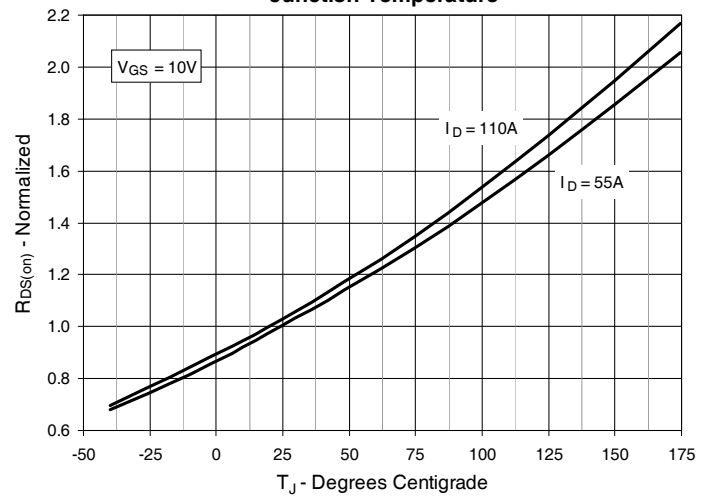


Fig. 5. $R_{DS(on)}$ Normalized to $I_D = 55\text{A}$ Value vs. Drain Current

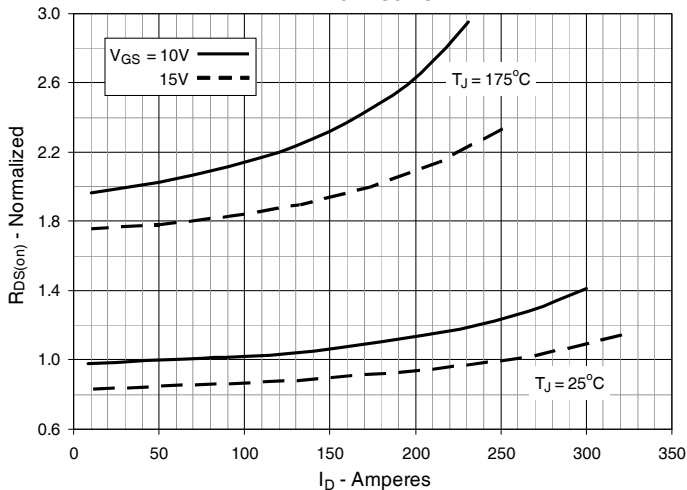


Fig. 6. Drain Current vs. Case Temperature

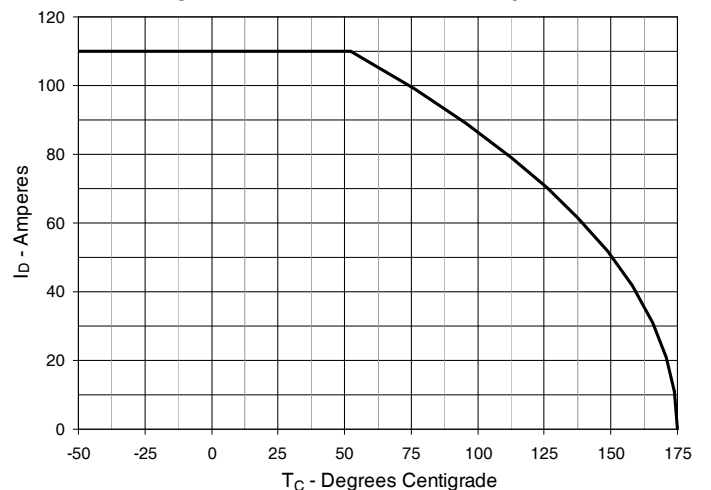


Fig. 7. Input Admittance

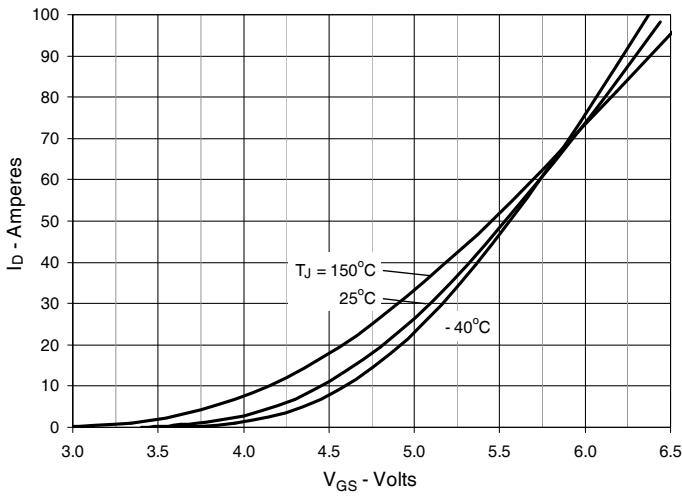


Fig. 8. Transconductance

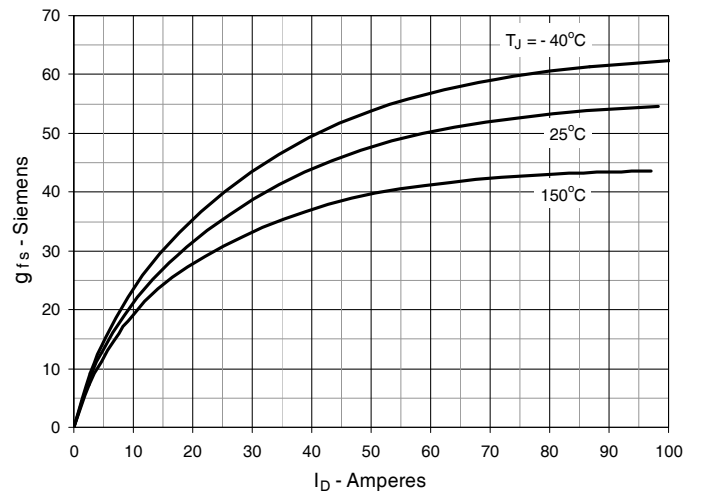


Fig. 9. Forward Voltage Drop of Intrinsic Diode

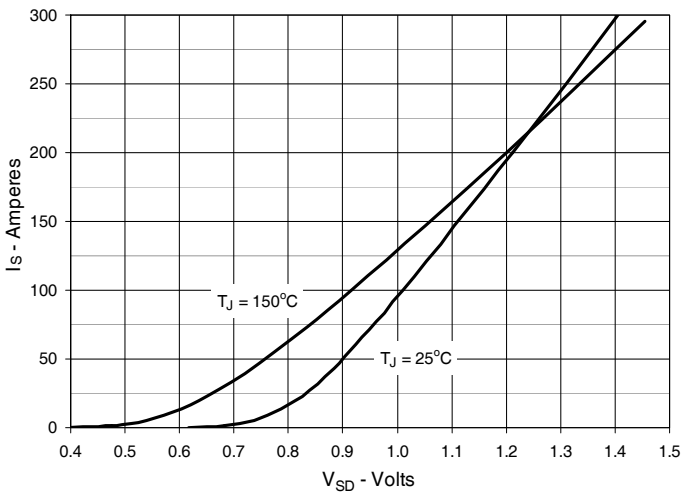


Fig. 10. Gate Charge

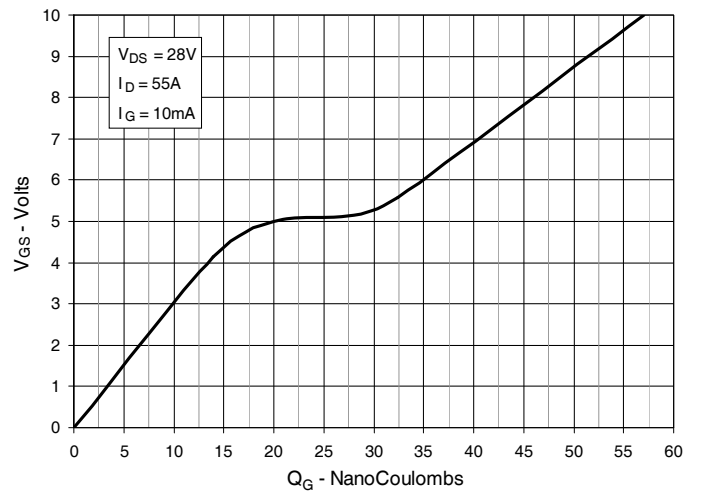


Fig. 11. Capacitance

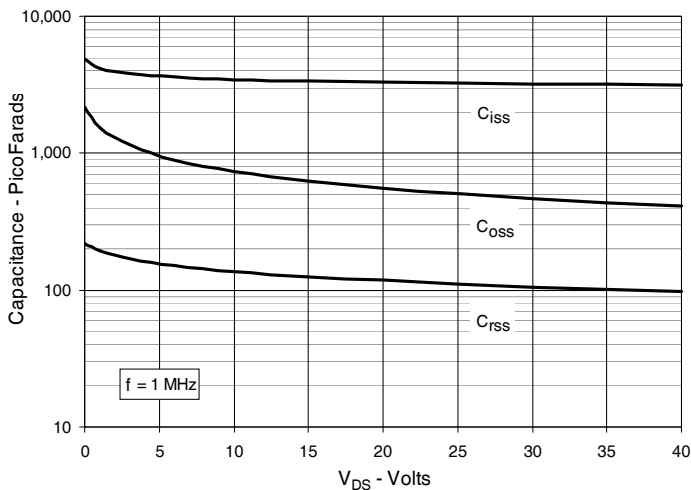


Fig. 12. Forward-Bias Safe Operating Area

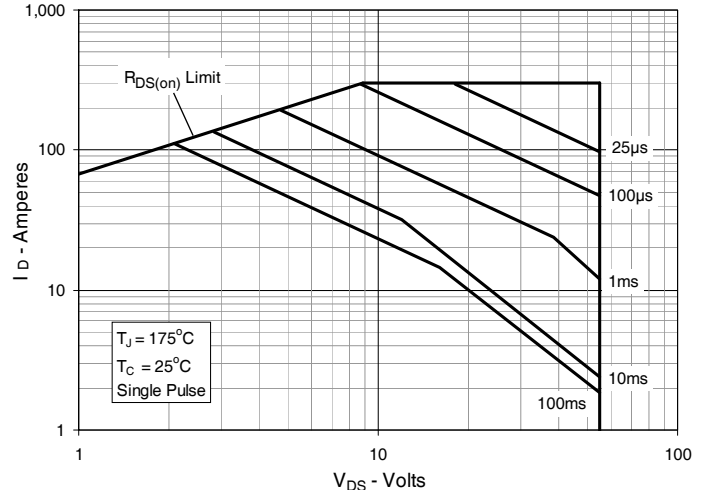


Fig. 13. Resistive Turn-on Rise Time vs. Junction Temperature

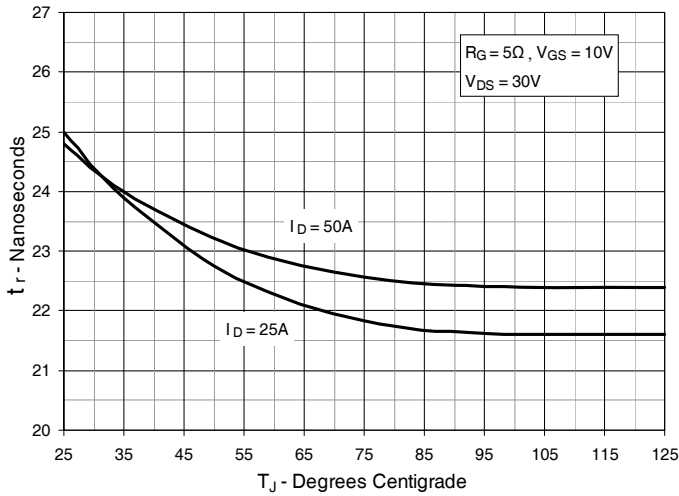


Fig. 14. Resistive Turn-on Rise Time vs. Drain Current

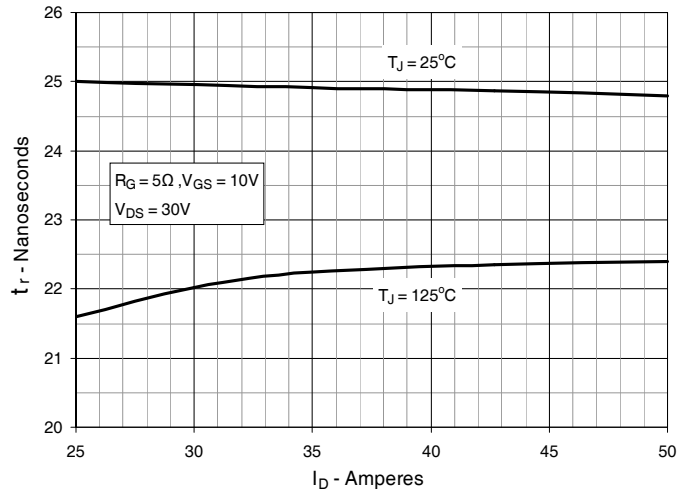


Fig. 15. Resistive Turn-on Switching Times vs. Gate Resistance

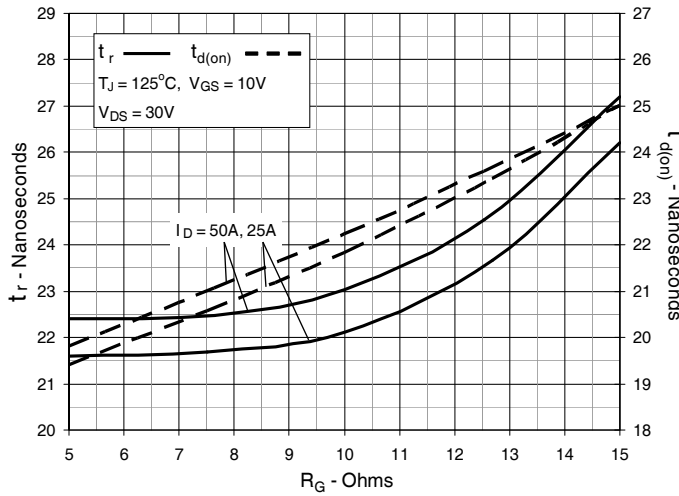


Fig. 16. Resistive Turn-off Switching Times vs. Junction Temperature

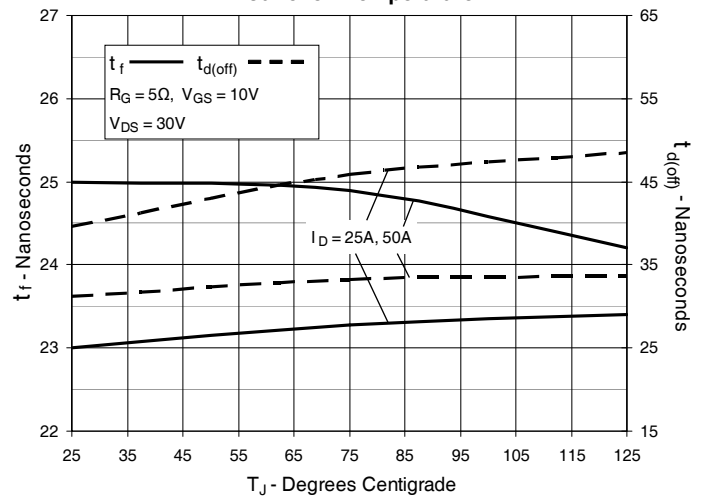


Fig. 17. Resistive Turn-off Switching Times vs. Drain Current

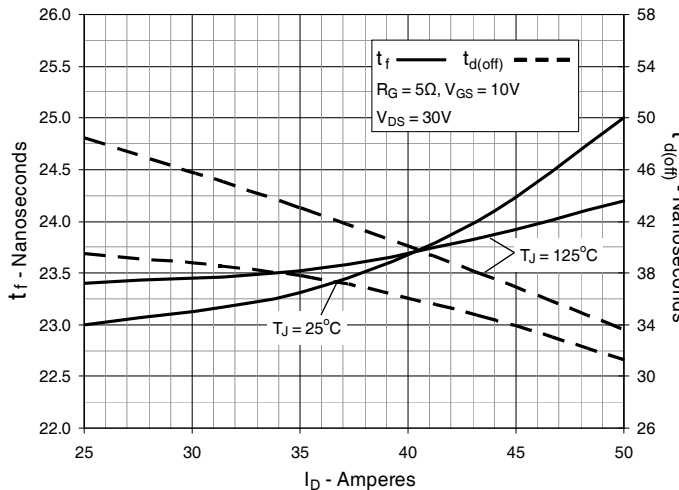


Fig. 18. Resistive Turn-off Switching Times vs. Gate Resistance

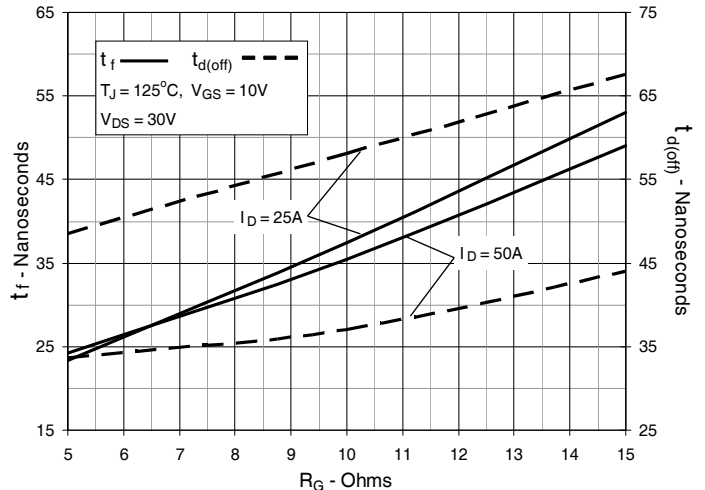
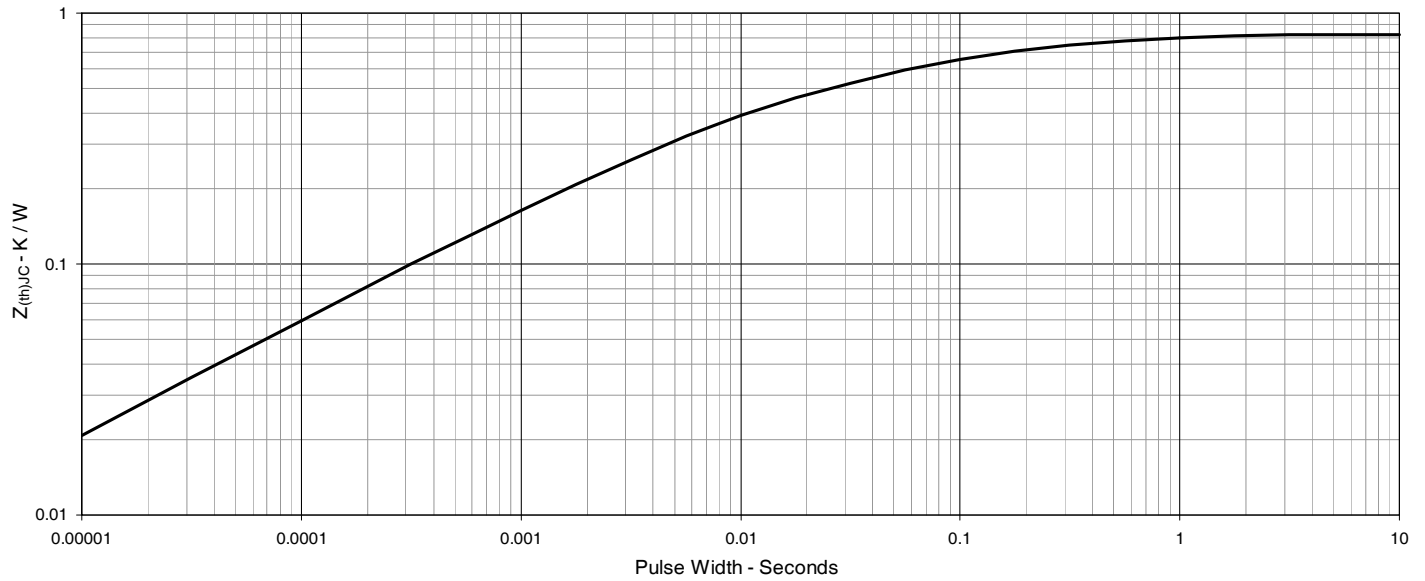


Fig. 19. Maximum Transient Thermal Impedance





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